United States Patent [19]

Kim et al.

[54] **METHOD FOR FILLING CONTACT HOLES WITH METAL BY TWO-STEP DEPOSITION**

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[57] **ABSTRACT**

Method for filling contact holes with metals by two-step deposition of selective tungsten layer is disclosed. The selective tungsten thin films are deposited in two steps, thus maximizing the contact filling with tungsten, gaining a stability of metal wires with better step coverage, and enhancing the reliability on semiconductor element.

5 Claims, 3 Drawing Sheets